

Electronic Supplementary Information

Improvement of external quantum efficiency depressed by visible light-absorbing hole transport material in solid-state semiconductor-sensitized heterojunction solar cells

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Table S1. Summary of all device performances.

		J_{sc} (mA/cm ²)	V_{oc} (mV)	FF (%)	η (%)
AIBN-0	1	11.3	552	61.6	3.9
	2	11.2	559	60.7	3.8
	3	11.1	559	57.2	3.5
	4	11.3	552	52.4	3.3
AIBN-4	1	11.9	566	66.7	4.5
	2	11.5	566	66.3	4.3
	3	11.7	559	66.7	4.4
	4	11.9	566	62.6	4.2
AIBN-8	1	11.5	566	59.7	3.9
	2	11.3	559	53.0	3.3
	3	11.8	559	52.3	3.4
	4	11.8	566	56.2	3.7

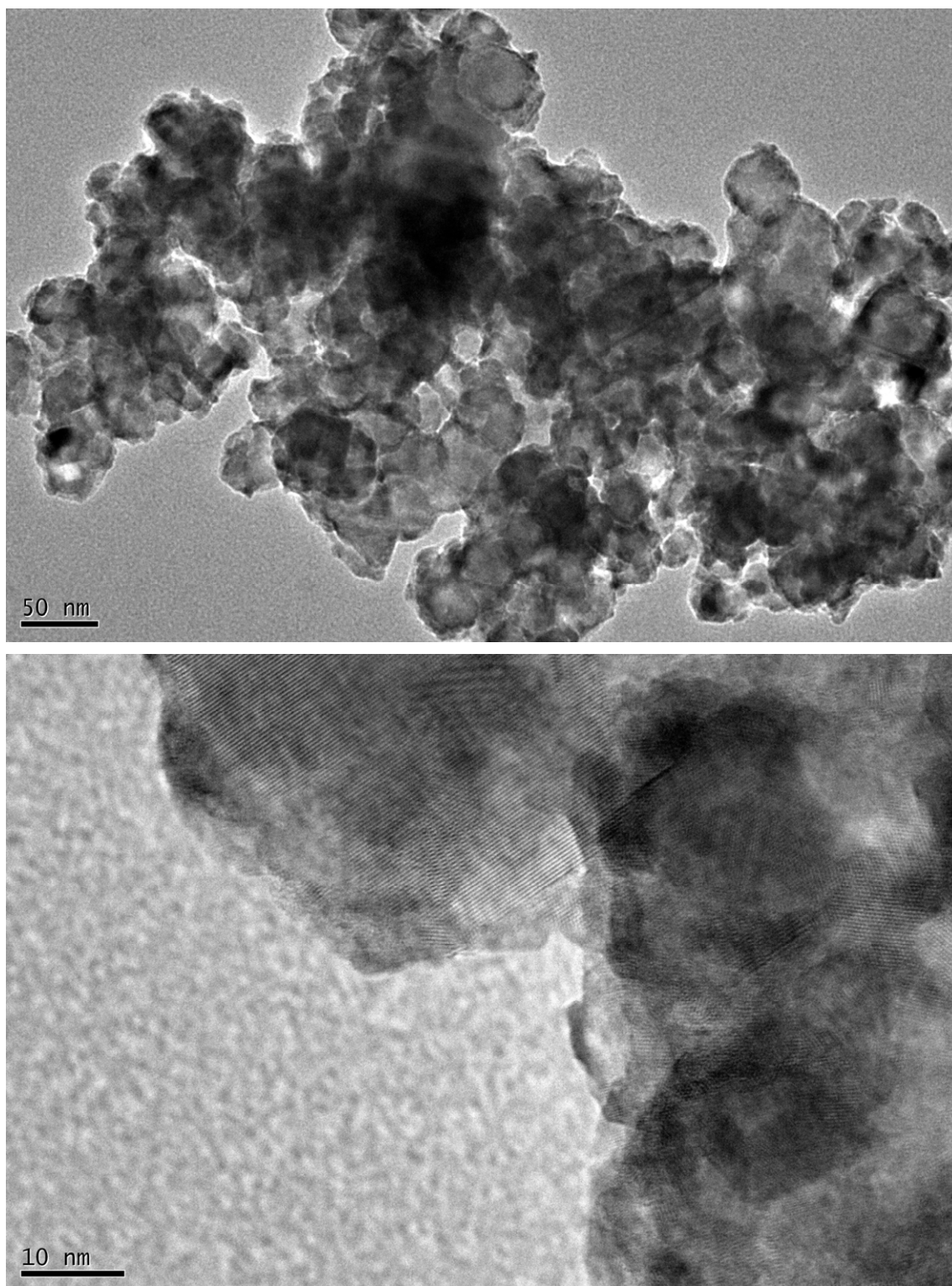


Figure S1. TEM images of Sb₂S₃ deposited on mp-TiO₂.